## **Supplementary Material:**

## Nonvolatile switchable half metallicity and magnetism in MXenes Hf<sub>2</sub>MnC<sub>2</sub>O<sub>2</sub>/Sc<sub>2</sub>CO<sub>2</sub> multiferroelectric heterostructure

Changwei Wu,<sup>\*a,b,c</sup> Shanwei Sun, <sup>c</sup> Weiping Gong, <sup>a,b</sup> Jiangyu Li, <sup>\*d</sup> Xiao Wang<sup>\*c</sup>

<sup>a</sup>Guangdong Provincial Key Laboratory of Electronic Functional Materials and Devices, Huizhou University, Huizhou 516001, P. R. China

<sup>b</sup>School of Electronic Information and Electrical Engineering, Huizhou University, Huizhou

516001, Guangdong, P. R. China

<sup>c</sup>Shenzhen Key Laboratory of Nanobiomechanics, Shenzhen Institute of Advanced Technology,

Chinese Academy of Sciences, Shenzhen 518055, P. R. China

<sup>d</sup>Guangdong Provincial Key Laboratory of Functional Oxide Materials and Devices, Department of Materials Science and Engineering, Southern University of Science and Technology, Shenzhen 518055, P. R. China

## **Corresponding authors**

Changwei Wu: cw.wu@hzu.edu.cn Jiangyu Li: lijy@sustech.edu.cn Xiao Wang: xiaowang@siat.ac.cn



**Figure S1.** (a) The atom structural diagrams of  $Sc_2CO_2$  monolayer with different polarization orientations. (b) Band structure of  $Sc_2CO_2$  monolayer. The gray, red and cyan balls represent C, O and Sc atoms, respectively. The green arrow represents the direction of polarization.



**Figure S2.** (a) The different stacking configurations of  $Hf_2MnC_2O_2/Sc_2CO_2$  heterostructures. (a) DW-(I), (b) DW-(II), (c) DW-(III) are for  $Hf_2MnC_2O_2/Sc_2CO_2\downarrow$ . (d) UP-(I), (e) UP-(II), (f) UP-(III) are for  $Hf_2MnC_2O_2/Sc_2CO_2\uparrow$ . C, O, Sc, Mn and Hf are represented by gray, red, cyan, blue and purple balls, respectively.

**Table S1**. Calculated parameters of  $Hf_2MnC_2O_2/Sc_2CO_2$  heterostructures. *d* is the interlayer distance.  $d_{0-0}$  is the minimum distance between O atom in  $Hf_2MnC_2O_2$  and O atom in  $Sc_2CO_2$ .  $d_{0-Sc}$  is the minimum distance between O atom in  $Hf_2MnC_2O_2$  and Sc atom in  $Sc_2CO_2$ .  $E_{tot}$  is the total energy.

Stacking Configurations	DW-(I)	DW-(II)	DW-(III)	UP-(I)	UP-(II)	UP-(III)
<i>d</i> (Å)	2.168	2.763	3.121	2.156	2.523	3.011
$d_{ ext{O-O}}\left(\text{\AA}\right)$	2.839	3.271	3.121	2.825	3.139	3.011
$d_{ ext{O-Sc}}( ext{\AA})$	2.815	3.932	4.294	2.775	3.698	4.072
$E_{tot} (\mathrm{eV})$	-104.200	-104.079	-104.028	-104.227	-104.151	-104.060



**Figure S3.** Electronic band structures of (a, b, e, f)  $Hf_2MnC_2O_2/Sc_2CO_2 P\downarrow$ , (c, d, g, h)  $Hf_2MnC_2O_2/Sc_2CO_2 P\uparrow$  with DFT-D2 and optPBE-vdW methods, respectively. Green and red lines represent the contributions from spin-up and spin-down channels of  $Hf_2MnC_2O_2$ , black lines denote the contributions from  $Sc_2CO_2$  monolayer.



**Figure S4.** The differential charge density of four structural states (a)  $P_1$ , (2) $P_2$ , (c)  $P_3$ , and (d)  $P_4$ . The green and purple colors represent charge depletion and accumulation, respectively.

**Table S2.** The magnetic anisotropic energy  $(MAE=E_{100}-E_{001})$  of Hf<sub>2</sub>MnC<sub>2</sub>O<sub>2</sub>/Sc<sub>2</sub>CO<sub>2</sub> heterostructure with different van der Waals corrections.

		$MAE = E_{100} - E_{001}$
	DFT-D3	-93 µeV
$Hf_2MnC_2O_2/Sc_2CO_2\downarrow$	DFT-D2	-97 μeV
	optPBE-vdw	-89 µeV
	DFT-D3	47 μeV
$Hf_2MnC_2O_2/Sc_2CO_2\uparrow$	DFT-D2	64 µeV
	optPBE-vdw	30 µeV



**Figure S5.** The d-orbital decomposed PDOS of (a)  $Hf_2MnC_2O_2$ , (b)  $Hf_2MnC_2O_2/Sc_2CO_2-P\downarrow$ , (c)  $Hf_2MnC_2O_2/Sc_2CO_2-P\uparrow$ . The Mn and Hf are represented by black and red colors, respectively.



**Figure S6.** The MAE of  $Hf_2MnC_2O_2/Sc_2CO_2-P\downarrow$  (red dot line) and  $Hf_2MnC_2O_2/Sc_2CO_2-P\uparrow$  (blue dot line) as function of the  $d_{O-Sc}$ . The red and blue dash vertical lines indicate equilibrium positions of  $Hf_2MnC_2O_2/Sc_2CO_2-P\downarrow$  and  $Hf_2MnC_2O_2/Sc_2CO_2-P\uparrow$ , respectively.